

**SECOND SEMESTER M.TECH. (ME) DEGREE END SEMESTER EXAMINATION****APRIL/MAY 2019****SUBJECT: LOW POWER VLSI DESIGN (ECE - 5221)****TIME: 3 HOURS****MAX. MARKS: 50****Instructions to candidates**

- Answer **ALL** questions.
- Missing data may be suitably assumed.

- 1A. List the components of dynamic power in VLSI and discuss the major factors affecting the power dissipation in each case.
- 1B. Explain the dynamic voltage scaling for reduction of power in VLSI with the help of a neat diagram. Also explain the significance of combined scaling of voltage and frequency. (5+5)
- 2A. With help of an example discuss how Shannon expansion can be used to implement Dynamic Supply gating? Explain the merits of Dynamic Supply gating.
- 2B. Discuss i) pre computation and ii) guarded evaluation strategy for reducing the dynamic power in computational blocks with suitable examples. (5+5)
- 3A. List and explain the factors that influence the leakage power in MOSFETs.
- 3B. Explain the advantages and disadvantages of MTCMOS circuits.
- 3C. Discuss the techniques used for lowering the leakage due to tunnelling. (4+3+3)
- 4A. What is the motivation for going for low swing buses? Explain. Also mention its limitations.
- 4B. What are the techniques employed to reduce the capacitance of interconnects? List and explain.
- 4C. Why do we make use of copper interconnects in today's VLSI? Give reasons. (4+3+3)
- 5A. Explain i) procrastination scheduling and ii) Object code compression technique for system level power reduction.
- 5B. Describe the fundamental principle of adiabatic switching and the conditions required for proper operation.
- 5C. Discuss the merits and demerits of predictive technique as a DPM policy. (4+3+3)